

DESCRIPTION

The 10155 is a 16-bit ECL Content Addressable Memory (CAM) organized as an array of 8 words by 2 bits. Each cell of the array consists of a D-type latch and an exclusive-OR comparator, along with control logic for reading, writing and masking.

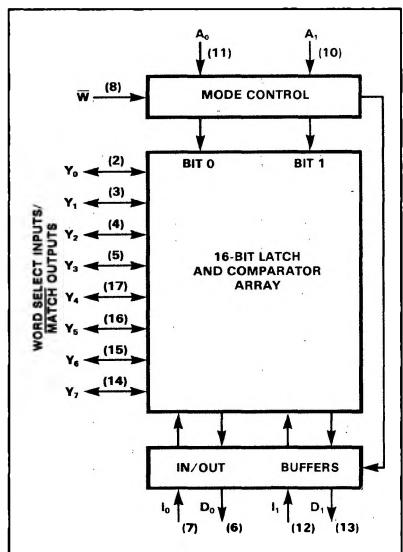
The modes of operation possible with the 10155 are associate, masked associate, read, write, and hybrid. Lines Y_0 - Y_7 are used for linear word select in the read/write mode, and are used as outputs for match/mismatch information in the associate mode.

In associate operation, I_0 and I_1 contain information to be compared. If the latches at a particular Y location are in a state matching the input data, that Y line goes low.

The Y outputs are open emitters, allowing expansion in multiples of 2 bits by tying additional 10155's to the Y bus lines. To inhibit comparison of a particular bit, the corresponding A_0 or A_1 line is held low.

In the read mode, the state of the selected cells appears on outputs D_0 and D_1 . In the write mode, these outputs are transparent, following the state of I_0 and I_1 .

In Hybrid mode, one of the I_0 or I_1 data inputs may be associated with the Q_{n0} or Q_{n1} cells respectively. If a match exists, the corresponding Y_n line(s) will go low, and can be used to address the other half of the memory for writing new data. Thus, it is possible to write I_1 in Q_{n1} where I_0 matches Q_{n0} or vice versa.

BLOCK DIAGRAM**FEATURES**

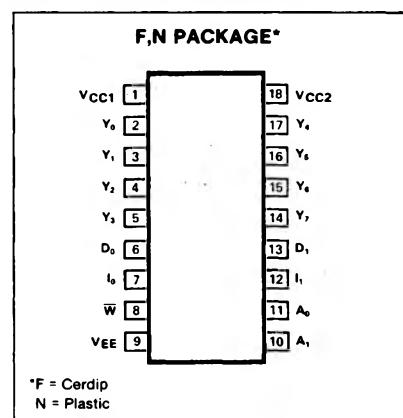
- 12ns associate time (max.)
- Linear address select
- Single bit masking
- 50Ω output drive
- ECL 10K compatible
- Open emitter match lines for easy bit expansion
- $50k\Omega$ input pulldown resistors (except on Y lines)

APPLICATION

- Content addressable memory systems

RECOMMENDED OPERATING VOLTAGES

- $V_{CC1} = V_{CC2} = 0V$
- $V_{EE} = -5.2V \pm 5\%$

PIN CONFIGURATION**TRUTH TABLE (POSITIVE LOGIC)**

MODE	A_0	A_1	I_0	I_1	\bar{W}	D_0	D_1	Q_{n0}	Q_{n1}	Y_n
Associate ¹	1	1	1/0	1/0	X	0	0	Q_{n0}	Q_{n1}	$Q_{n0} \oplus I_0 + Q_{n1} \oplus I_1$
Associate ^{1,2} (masked)	1	0	1/0	X	1	0	D_1	Q_{n0}	Q_{n1}	$Q_{n0} \oplus I_0$
Associate ^{1,2} (masked)	0	1	X	1/0	1	D_0	0	Q_{n0}	Q_{n1}	$Q_{n1} \oplus I_1$
Read ³	0	0	X	X	1	D_0^2	D_1^2	Q_{n0}	Q_{n1}	0 (Selected address)
Write ^{3,4}	0	0	1/0	1/0	0	I_0	I_1	I_0	I_1	0 (Selected address)
Hybrid ⁵	1	0	1/0	1/0	0	0	I_1	Q_{n0}	$I_1 \cdot \bar{Y}_n$	$Q_{n0} \oplus I_0$
Hybrid ⁵	0	1	1/0	1/0	0	I_1	0	$I_0 \cdot \bar{Y}_n$	Q_{n1}	$Q_{n1} \oplus I_1$

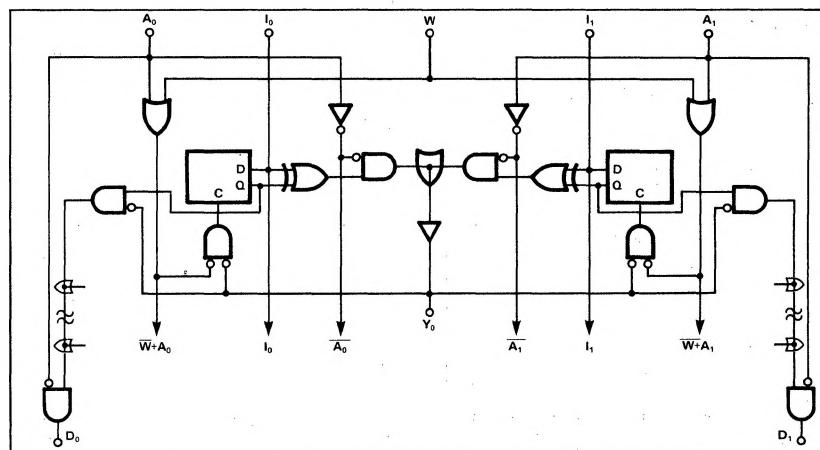
X = Don't care

Q_{n0} = Contents of address n, Bit 0 (n = 0 to 7)

Q_{n1} = Contents of address n, Bit 1

NOTES

1. 1 (high) = Mismatch, 0 (low) = Match
2. Read mode: $D_0 = Q_{00} \cdot \bar{Y}_0 + Q_{10} \cdot \bar{Y}_1 + \dots + Q_{70} \cdot \bar{Y}_7$
 $D_1 = Q_{01} \cdot \bar{Y}_0 + Q_{11} \cdot \bar{Y}_1 + \dots + Q_{71} \cdot \bar{Y}_7$
3. In normal operation a single Y address is selected for read or write
4. Write is transparent
5. Simultaneous Associate and Write at all "Match" addresses.

LOGIC DIAGRAM (TYPICAL BIT)

ABSOLUTE MAXIMUM RATINGS $V_{CC1} = V_{CC2} = 0V$

PARAMETER		RATING	UNIT
V_{EE}	Supply voltage	-8	Vdc
V_{IN}	Input voltage	0 to V_{EE}	Vdc
I_o	Output source current	40	mAdc
	Temperature Range		°C
T_A	Operating	-30 to +85	
T_J	Operating junction	125	
T_{STG}	Storage	-55 to +125	

DC ELECTRICAL CHARACTERISTICS¹ $V_{CC1} = V_{CC2} = 0V$, $V_{EE} = -5.2V$, $R_L = 50\Omega$ to -2V

PARAMETER	TEST CONDITIONS	-30 °C			+25 °C			+85 °C			UNIT
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
V_{IL}	Input voltage Low	-1.890			-1.850			-1.825			V
V_{IH}	High				-0.890			-0.810			
V_{ILA}	Low threshold				-1.500			-1.475			
V_{IHA}	High threshold	-1.205			-1.105			-1.035			
V_{OL}	Output voltage Low	-1.89			-1.675	-1.65	-1.70	-1.85	-1.825		V
V_{OH}	High	-1.06			-0.89	-0.96	-0.89	-0.81	-0.89		
V_{OLA}	Low threshold				-1.655			-1.63			
V_{OHA}	High threshold				-0.98			-0.91			
I_{IL}	Input current Low				0.5						μA
I_{IH}	High							220			
								200			
								50			
I_{EE}	Supply current							115	140		mA

AC ELECTRICAL CHARACTERISTICS² $-30^\circ C \leq T_A \leq +85^\circ C$, $V_{CC1} = V_{CC2} = +2V$, $V_{EE} = -3.2V$, $R_L = 50\Omega$ to ground

PARAMETER	FROM	TO	TEST CONDITIONS	LIMITS			UNIT	
				Min ³	Typ ⁴	Max		
Associate time T_{A1} T_{A2}	I^\pm A^+	Y^\pm Y^+			8 9	12 12	ns	
Disable time T_{D1} T_{D2} T_{D3}	A^- A^+ Y^+	Y^- D^- D^-			8 4 9	12 7 13	ns	
Setup and hold time T_{H1} Hold time T_{S2} Setup time T_{H2} Hold time T_{S3} Setup time T_{H3} Hold time T_{S4} Setup time	\overline{W}^+ $A-$ \overline{W}^+ Y^+ \overline{W}^+ I^\pm	A^+ Y^- Y^\pm \overline{W}^- I^\pm \overline{W}^+		1 15 3 3 3 5	0 11 1 2 1 3		ns	
Tw Write pulse width					10	5		ns
Access time T_{A3} Write T_{A4} Write T_{A5} Read T_{A6} Read	\overline{W}^- $I^{+,-}$ Y^- A^-	D^\pm $D^{+,-}$ D^+ D^+	$T_{S4} \geq Tw$		13 9 6 4	17 13 10 4		ns

NOTES

1. Each ECL 10K series device has been designed to meet the dc and ac specifications after thermal equilibrium has been established. The circuit is in a test socket or mounted on a printed circuit board and transverse air flow greater than 500 linear fpm is maintained.

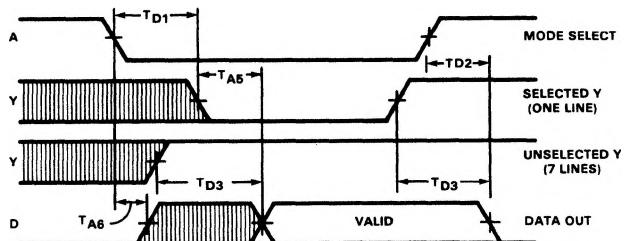
2. Refer to dc characteristics.

3. Minimum allowed.

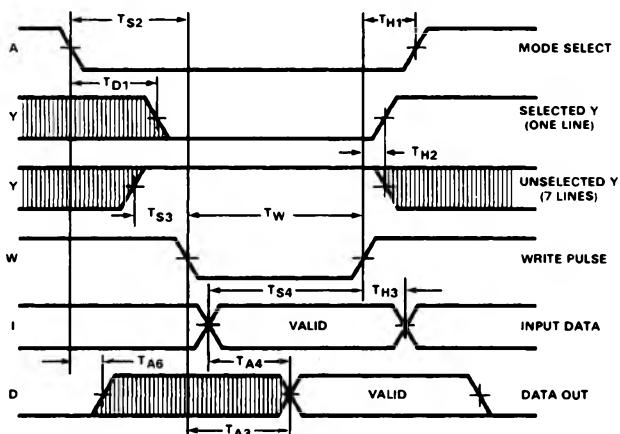
4. All typical values are at $T_A = +25^\circ C$.

VOLTAGE WAVEFORMS

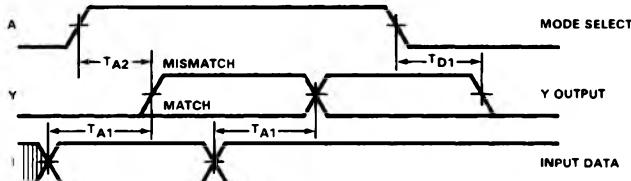
READ CYCLE



WRITE CYCLE



ASSOCIATE CYCLE



MEASUREMENT CIRCUIT

